cojc FY

PTO/SB/21 (08-00)

MAY 2 4 2007 W

indicated below.

Signature

Type or printed name

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Application Number 09/832,844

Filing Date April 12, 2001

First Named Inventor Shunpei YAMAZAKI

Group Art Unit 2826

Examiner Name M. Tran

Attorney Docket Number 0756-2288

Total Number of Pages in This	Submission	1	Attorney Docket Number	er 0756-2288			
ENCLOSURES (check all that apply)							
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53				After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosures 1. Request for Certificate of Correction and Form PTO1050 2. 3. 4. 5. 6. shereby authorized to charge any additional voverpayments to Deposit Account No. 50-ied docket number.			
	SIGNATUR	RE OF APPL	LICANT, ATTORNEY, O	DR AGENT			
Firm or Individual name	Eric J. Robinson, Reg. No. 38,285 Robinson Intellectual Property Law Office, P.C. PMB 955 21010 Southbank Street Potomac Falls, VA 20165 Certificate MAY 2 9 2007 Of Correction						
Signature	5:			of Correction			
Date	May 22, 2007						
		CERTIFI	CATE OF MAILING				
I hereby certify that this corresp class mail in an envelope addre	ondence is bei	ing deposited missioner for I	with the United States Post Patents, P.O. Box 1450, Ale	tal Service with sufficient postage as first exandria, VA 22313-1450 on the date			

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date

May 22, 2007

Adele M. Stamper

ONE	E 18025
MAY '	2 4 2007 y
TO TE	ADEMART

TRANSMITTAL FORM

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

Group Art Unit 2826

Examiner Name M. Tran

Attorney Docket Number 0756-2288

09/832,844		
April 12, 2001		
Shunpei YAMAZAKI		
2826		
M. Tran		
0756-2288		

PTO/SB/21 (08-00)

		ENCLOSURES (check all that appl	y)			
Fee Transmittal Form Fee Attached Amendment / Reply After Final Affidavits/declaration(s) Extension of Time Request Express Abandonment Request Information Disclosure Statement Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53		Assignment Papers (for an Application) Drawing(s) Declaration and Power of Attorney Licensing-related Papers Petition Petition to Convert to a Provisional Application Power of Attorney, Revocation Change of Correspondence Address Terminal Disclaimer Request for Refund CD, Number of CD(s) Remarks The Commissioner is fees required or credit any 2280 for the above identific	After Allowance Communication to Group Appeal Communication to Board of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Proprietary Information Status Letter Other Enclosures 1. Request for Certificate of Correction and Form PTO1050 2. 3. 4. 5. 6.			
	1	RE OF APPLICANT, ATTORNEY, O	R AGENT			
Firm or	Robinson	Intellectual Property Law Office, P.C.				
Individual name	PMB 955 21010 Southbank Street Potomac Falls, VA 20165					
Signature	<i>\\</i>					
Date	May 22, 2007					
		CERTIFICATE OF MAILING				
I hereby certify that this corresp class mail in an envelope addre indicated below.	ondence is be ssed to: Com	ing deposited with the United States Post missioner for Patents, P.O. Box 1450, Ale	al Service with sufficient postage as first exandria, VA 22313-1450 on the date			
Type or printed name	Ade	le M. Stamper				
Signature		delim Stampy	Date May 22, 2007			

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Attorney Docket No. 0756-2288

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:) Group Art Unit: 2826
Shunpei YAMAZAKI) Examiner: M. Tran
Patent No.: 7,067,844) <u>CERTIFICATE OF MAILING</u> I hereby certify that this correspondence is
Dated: June 27, 2006	being deposited with the United States Postal Service with sufficient postage as First Class
Serial No. 09/832,844) Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450,
Filed: April 12, 2001) Alexandria, VA 22313-1450, on May 22, 2007.

REQUEST FOR CERTIFICATE OF CORRECTION UNDER 37 CFR § 1.322 FOR **CORRECTION OF OFFICE MISTAKE**

ATTN: Certificate of Correction Branch Honorable Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

For: ELECTRO-OPTICAL DEVICE

Sir:

As provided in detail in the attached, the patentee respectfully requests that a Certificate of Correction be granted in the above-identified patent to correct a mistake in a patent, incurred through the fault of the Office.

Under 37 CFR 1.322, "The Commissioner may issue a certificate of correction pursuant to 35 U.S.C. 254 to correct a mistake in a patent, incurred through the fault of the Office, which mistake is clearly disclosed in the records of the Office at the request of the patentee or the patentee's assignee."

The Patentee furthermore requests Expedited Issuance of this Certificate of Correction in accordance with MPEP § 1480.01. Specifically, this section provides that:

In an effort to reduce the overall time required in processing and granting Certificate of Correction requests, the Office will expedite processing and granting of patentee requests where such requests are accompanied by evidence to show that the error is attributable solely to the Office Where the correction requested was incurred through the

fault of the Office, and the matter is clearly disclosed in the records of the Office, and is accompanied by documentation that unequivocally supports the patentee's assertion(s), a Certificate of Correction will be expeditiously issued. MPEP § 1480.01

The following errors appear to have occurred through the fault of the Office, and the patentee respectfully requests correction thereof.

The Applicant filed a *Correction to Prior Information Disclosure Statement* on May 16, 2001 (received by OIPE May 18, 2001), a copy of which is attached. In the *Correction*, the Applicant corrected the page numbers for a non-patent literature reference, i.e. Hatalis et al., "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films", August 1987, pp. 361-364, IEEE Electron Device Letters, Vol. EDL-8, No. 8 (emphasis added). The corrected citation was included in an attached Form PTO-1449. Also, the *Correction* specifically included a request to "line through the incorrect reference and consider the corrected reference as indicated on the revised Form PTO-1449 submitted herewith" (emphasis added).

In response, the Examiner accepted this correction as noted in the Official Action mailed May 21, 2002, and evidenced by an initialed Form PTO-1449 attached to the Official Action, a copy of which is attached. However, the Examiner apparently overlooked the instruction to strike through the incorrect citation. Also, this oversight was not corrected by the Office when the application was prepared for issuance and publication as a patent.

As a result, there are two citations of the Hatalis article on the issued patent, only one of which is correct. Specifically, at page 3, column 2, under the heading "OTHER PUBLICATIONS," lines 3-6, the correct citation for the Hatalis article appears. However, at page 4, column 1, lines 26-29, an incorrect citation for the Hatalis article appears as "Hatalis et al., 'High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films', Aug. 1987, pp. 161-164, IEEE Electron

Patent No. 7,067,844 Application Serial No. 09/832,844 Attorney Docket No. 0756-2288

Device Letters, vol. EDL-8, No. 8." (emphasis added). Since the second citation of the Hatalis article appears to have been included in the issued patent as the result of Patent Office error, the patentee respectfully requests that the issued patent be corrected by deleting the second citation of the Hatalis article at page 4, column 1, lines 26-29.

As the error was incurred through the fault of the Office, a fee is not believed to be necessary. Should it be determined that a fee is necessary, any deficiencies or overages in any fees due in connection with this patent and the requested actions should be applied to Deposit Account No. 50-2280(0756-2288).

Respectfully submitted,

Eric J. Robinson

Reg. No. 38,285

Robinson Intellectual Property Law Office, P.C. PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO : 7,067,844

DATED : June 27, 2006

INVENTOR(S): Shunpei YAMAZAKI

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the "References Cited" section (56):

At page 4, column 1, lines 26-29, delete the following:

Hatalis et al., "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films", Aug. 1987, pp. 161-164, IEEE Electron Device Letters, vol. EDL-8, No. 8.

MAILING ADDRESS OF SENDER:

Eric J. Robinson
Robinson Intellectual Property Law Office
PMB 955
21010 Southbank Street
Potomac Falls, VA 20165

No. of additional copies

PATENT NO. 7,098,479

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

•

ocket No.: 740756-2288

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of:) Sisteme or
Shunpei YAMAZAKI) Art Unit: Unassigned 8-24-01
Serial No.: 09/832,844) Examiner: Unassigned
Filed: April 12, 2001)
For: ELECTRO-OPTICAL DEVICE AND)
METHOD FOR MANUFACTURING)
THE SAME) · · · · · · · · · · · · · · · · · · ·
	TE OF MAILING

CORRECTION TO PRIOR INFORMATION DISCLOSURE STATEMENT

with sufficient postage as First Class Mail in an envelope Patents, Washington, D.C. 20231, on May 16, 2001.

Commissioner for Patents Washington, D.C. 20231

Sir:

In an "Information Disclosure Statement and Notification of Related Applications" filed April 12, 2001, Form PTO-1449 contained the following typographical errors:

U.S. Patent No. 4,849,797 was listed twice. Once correctly and once incorrectly as 4,894,797. It is requested that the Examiner line through the incorrect Patent, namely 4,894,797.

Japanese Laid-Open Patent No. 02-210330 was listed twice. Once correctly and once incorrectly as 02-120330. It is requested that the Examiner line through the incorrect Patent, namely 02-120330.

Pages 361-364 of the IEEE Electron Device Letters "High Performance Thin Film Transistors in Low-Temperature Crystallized LPCVD Amorphous Silicon Films" written by Hatalis, were incorrectly cited as pages 161-164. Please line through the incorrect reference and consider the corrected reference as indicated on the revised Form PTO-1449 submitted herewith.

Copies of the above-mentioned references have already been provided and are not submitted herewith.

. .

The English Language Abstract of Japanese Laid-Open Patent No. 60-245174 was previously submitted with the aforementioned Information Disclosure Statement. Full English Translation of this reference is submitted herewith in accordance with 37 C.F.R. 1.98(a).

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the references listed on the attached Form PTO-1449 be made of record in the above-identified application.

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 19-2380.

Respectfully submitted,

Eric J. Robinson

Registration No. 38,285

NIXON PEABODY LLP 8180 Greensboro Drive, Suite 800 McLean, Virginia 22102 (703) 790-9110

Form PTO-1 (Rev. 8-83)		ent of Commerce Trademark Office	Atty Docket 0756-22		Serial No. 09	9/832,844	
/ *	HORMATON DISCLOSURE STATE	MENT	Applicants: Shunpei YAM	IAZAKI	•	#4	-
	HAY 1 8 JUM &	Filing Date: April 12, 2001		Group Art U	Jnit:-N/A	28.	
P.		REIGN PATEN	IT DOCUMENTS				
Examiner	TRADE Document Number	Date	Country	Class	Subclass	Transla	tion
Initial		·				Yes	No
MLT	60-245174	12/04/1985	JP	<u> </u>		Full Eng	
•	OTHER DO	OCUMENTS ((Including Author, Title, Date, Per	tinent Page:	s, Etc.)		
Examiner Initial			,				
MLT	Hatalis et al., "High Performance Thin Fi Films", August 1987, pp. 361-364, IEEE	lm Transistors ir Electron Device	Low-Temperature Crystalliz Letters, Vol. EDL-8, No. 8	zed LPCVI	Amorphous S	ilicon	19
	Munhloan		Date Considered 5		HAY 23 2001 TC 1700 MAIL ROOM		
	/			100			_
	Mus la locus		=	17)-1			- 11

05/15/2001